

section of the wafer rotary means, and the annular gap defined between these edges is at very small intervals to prevent chemical fluids and purified water from being leaked downward.

13. (Amended) The single wafer type substrate cleaning apparatus according to any of Claims 4 to 10, wherein the chemical fluid supply section consists of injection nozzles for injecting and supplying cleaning fluid to the face of each wafer which is supported by the wafer rotary means from above, and the injection nozzles are provided to be horizontally turnable while directed downward, and inject and supply the cleaning fluid to the face of each wafer which is rotatably supported by the wafer rotary means while it is turned horizontally from the outer peripheral portion toward the center thereof or in standstill position as it is horizontally turned.

14. (Amended) The single wafer type substrate cleaning apparatus according to any of Claims 4 to 10, wherein the inert gas is a nitrogen gas.